

**Product data sheet** 

### 1. General description

PNP low  $V_{CEsat}$  Breakthrough In Small Signal (BISS) transistor, encapsulated in an ultra thin SOT1061 leadless small Surface-Mounted Device (SMD) plastic package with medium power capability.

NPN complement: PBSS4330PA.

### 2. Features and benefits

- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability I<sub>C</sub> and I<sub>CM</sub>
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors
- Exposed heat sink for excellent thermal and electrical conductivity
- · Leadless small SMD plastic package with medium power capability

### 3. Applications

- Loadswitch
- Battery-driven devices
- Power management
- Charging circuits
- Power switches (e.g. motors, fans)

### 4. Quick reference data

Table 1. Quick reference data							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-	-30	V
I <sub>C</sub>	collector current			-	-	-3	А
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	-	-5	А
R <sub>CEsat</sub>	collector-emitter saturation resistance	I <sub>C</sub> = -3 A; I <sub>B</sub> = -300 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02 ; T <sub>amb</sub> = 25 °C		-	75	107	mΩ

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# 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	3	3
2	E	emitter		1
3	С	collector		2
				sym013
			Transparent top view DFN2020-3 (SOT1061)	

# 6. Ordering information

Table 3.         Ordering information					
Type number Package					
	Name	Description	Version		
PBSS5330PA	DFN2020-3	DFN2020-3: plastic thermal enhanced ultra thin small outline package; no leads; 3 terminals; body 2 x 2 x 0.65 mm	SOT1061		

### 7. Marking

Table 4. Marking codes	
Type number	Marking code
PBSS5330PA	AJ

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### 8. Limiting values

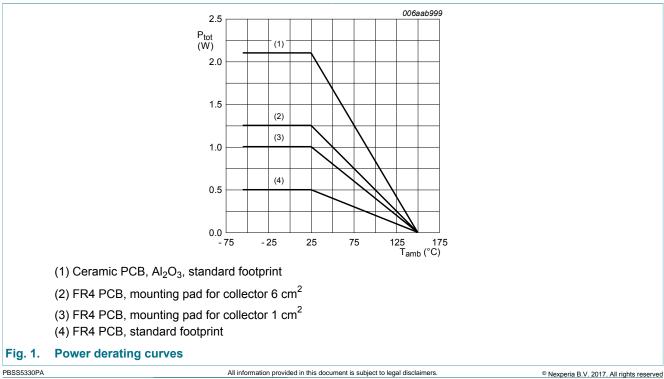
#### Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	-30	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-30	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	-6	V
I <sub>C</sub>	collector current			-	-3	А
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	-5	А
I <sub>B</sub>	base current			-	-500	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	500	mW
			[2]	-	1	W
			[3]	-	1.25	W
			[4]	-	2.1	W
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

- <sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- <sup>[3]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.
- [4] Device mounted on a ceramic PCB,  $Al_2O_3$ , standard footprint.

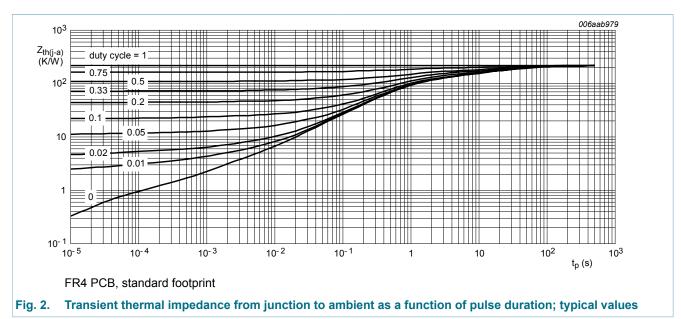


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### 9. Thermal characteristics

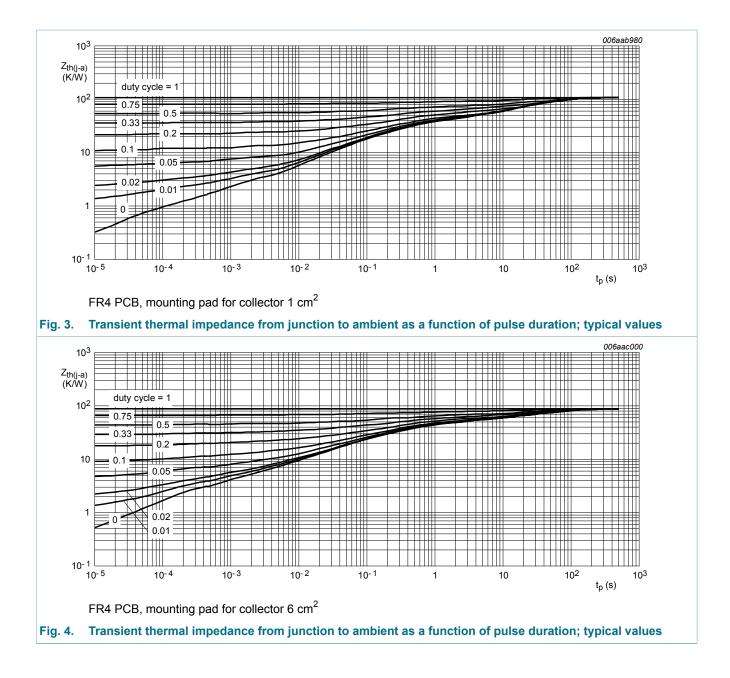
Table 6. Thermal characteristics							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub> thermal resistance from junction to ambient	in free air	[1]	-	-	250	K/W	
		[2]	-	-	125	K/W	
		[3]	-	-	100	K/W	
			[4]	-	-	60	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.
- [4] Device mounted on a ceramic PCB,  $Al_2O_3$ , standard footprint.





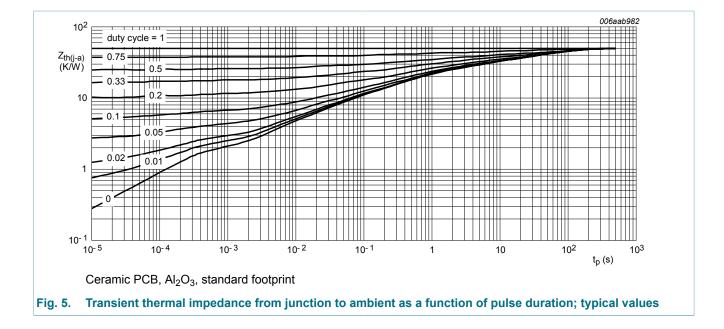
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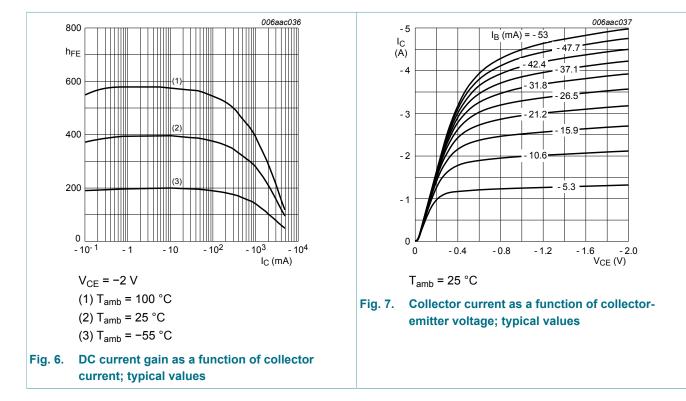
### **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off	$V_{CB}$ = -30 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
	current	$V_{CB}$ = -30 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	-50	μA
I <sub>CES</sub>	collector-emitter cut-off current	$V_{CE}$ = -24 V; $V_{BE}$ = 0 V; $T_{amb}$ = 25 °C	-	-	-100	nA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB}$ = -5 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
h <sub>FE</sub>	DC current gain	$\begin{split} &V_{CE} \texttt{=-2 V; I}_{C} \texttt{=-0.5 A; pulsed;} \\ &t_{p} \texttt{\leq 300 } \mu\texttt{s; } \delta \texttt{\leq 0.02 }; T_{amb} \texttt{= 25 }^{\circ}\texttt{C} \end{split}$	200	320	-	
		$\begin{split} V_{CE} &= -2 \text{ V}; \text{ I}_{C} = -1 \text{ A}; \text{ pulsed}; \\ t_{p} &\leq 300  \mu\text{s};  \overline{\delta} &\leq 0.02 ;  T_{amb} = 25 ^{\circ}\text{C} \end{split}$	175	280	450	
	$V_{CE}$ = -2 V; I <sub>C</sub> = -2 A; pulsed; t <sub>p</sub> ≤ 300 µs; $\overline{\delta}$ ≤ 0.02 ; T <sub>amb</sub> = 25 °C	140	210	-		
		$V_{CE} = -2 \text{ V; } I_C = -3 \text{ A; pulsed;}$ $t_p \le 300  \mu\text{s; } \overline{\delta} \le 0.02 \text{ ; } T_{amb} = 25 ^\circ\text{C}$	100	160	-	
V <sub>CEsat</sub> collector-emitter saturation voltage		$\begin{split} I_C &= -0.5 \text{ A};  I_B = -50 \text{ mA}; \text{ pulsed}; \\ t_p &\leq 300  \mu\text{s};  \delta \leq 0.02  ;  T_{\text{amb}} = 25 ^\circ\text{C} \end{split}$	-	-45	-70	mV
		$\begin{split} I_C &= -1 \text{ A};  I_B = -50 \text{ mA}; \text{ pulsed}; \\ t_p &\leq 300  \mu\text{s};  \delta \leq 0.02  ;  T_{amb} = 25 ^\circ\text{C} \end{split}$	-	-90	-130	mV
		$\begin{split} I_{C} &= -2 \text{ A};  I_{B} = -100 \text{ mA}; \text{ pulsed}; \\ t_{p} &\leq 300  \mu\text{s};  \overline{\delta} &\leq 0.02  ;  T_{amb} = 25 ^{\circ}\text{C} \end{split}$	-	-170	-240	mV
		$I_{C}$ = -3 A; $I_{B}$ = -300 mA; pulsed;	-	-230	-320	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	$t_p$ ≤ 300 μs; δ ≤ 0.02 ; T <sub>amb</sub> = 25 °C	-	75	107	mΩ
V <sub>BEsat</sub>	base-emitter saturation voltage	$\begin{split} I_{C} &= -2 \text{ A};  I_{B} = -100 \text{ mA}; \text{ pulsed}; \\ t_{p} &\leq 300  \mu\text{s};  \delta \leq 0.02  ;  T_{amb} = 25 ^{\circ}\text{C} \end{split}$	-	-0.89	-1.1	V
		$\begin{split} I_C &= -3 \text{ A};  I_B = -300 \text{ mA}; \text{ pulsed}; \\ t_p &\leq 300  \mu\text{s};  \delta \leq 0.02  ;  T_{\text{amb}} = 25 ^\circ\text{C} \end{split}$	-	-0.97	-1.2	V
V <sub>BEon</sub>	base-emitter turn-on voltage	$V_{CE}$ = -2 V; I <sub>C</sub> = -1 A; pulsed; t <sub>p</sub> ≤ 300 µs; $\delta$ ≤ 0.02 ; T <sub>amb</sub> = 25 °C	-	-0.75	-1	V
t <sub>d</sub>	delay time	V <sub>CC</sub> = -9 V; I <sub>C</sub> = -2 A; I <sub>Bon</sub> = -0.1 A;	-	11	-	ns
t <sub>r</sub>	rise time	$I_{Boff}$ = 0.1 A; $T_{amb}$ = 25 °C	-	59	-	ns
t <sub>on</sub>	turn-on time		-	70	-	ns
t <sub>s</sub>	storage time		-	165	-	ns
t <sub>f</sub>	fall time		-	35	-	ns
t <sub>off</sub>	turn-off time		-	200	-	ns

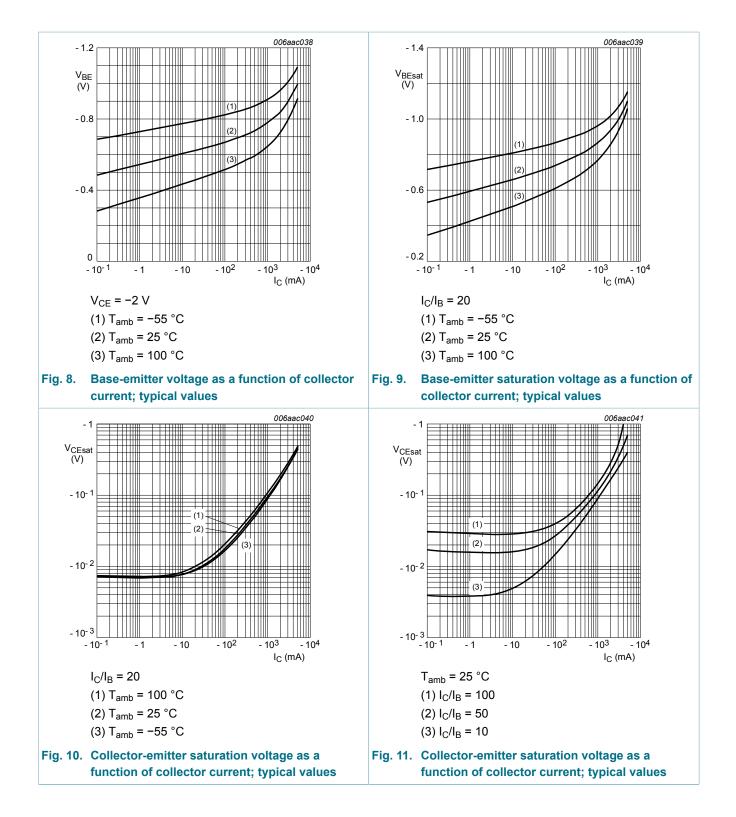
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f <sub>T</sub>	transition frequency	$V_{CE}$ = -5 V; I <sub>C</sub> = -100 mA; f = 100 MHz; T <sub>amb</sub> = 25 °C	100	165	-	MHz
C <sub>c</sub>	collector capacitance	V <sub>CB</sub> = -10 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C	-	38	45	pF



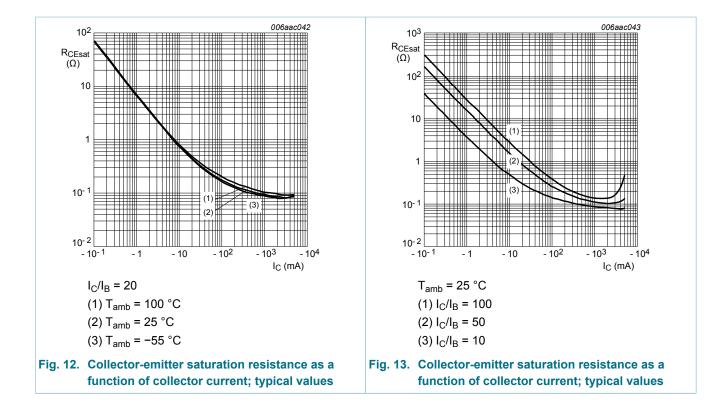
#### 30 V, 3 A PNP low VCEsat (BISS) transistor



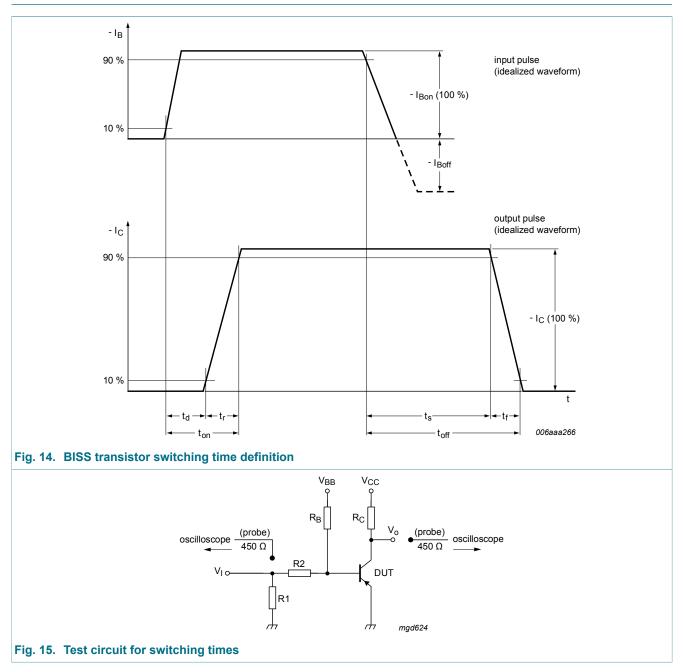
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# PBSS5330PA

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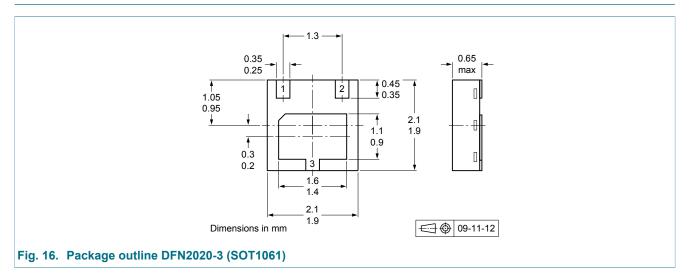
#### 30 V, 3 A PNP low VCEsat (BISS) transistor



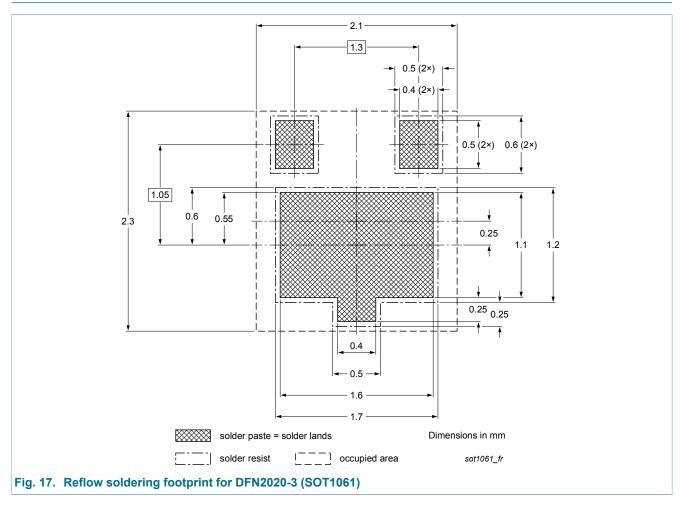
### **11. Test information**

#### 30 V, 3 A PNP low VCEsat (BISS) transistor

### 12. Package outline



### 13. Soldering



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# 14. Revision history

Table 8. Revision hi	story			
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS5330PA v.2	20150407	Product data sheet	-	PBSS5330PA v.1
Modifications:	Condition V <sub>CE</sub> chan	ged for parameter I <sub>CES</sub> in	Table 7, Characteristics	
PBSS5330PA v.1	20100419	Product data sheet	-	-

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### 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [ <u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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